

1.本站收集的数据手册和产品资料都来自互联网,版权归原作者所有。如读者和版权方有任 何异议请及时告之,我们将妥善解决。

本站提供的中文数据手册是英文数据手册的中文翻译,其目的是协助用户阅读,该译文无法自动跟随原稿更新,同时也可能存在翻译上的不当。建议读者以英文原稿为参考以便获得更精准的信息。

3.本站提供的产品资料,来自厂商的技术支持或者使用者的心得体会等,其内容可能存在描 叙上的差异,建议读者做出适当判断。

4.如需与我们联系,请发邮件到marketing@iczoom.com,主题请标有"数据手册"字样。

Read Statement

1. The datasheets and other product information on the site are all from network reference or other public materials, and the copyright belongs to the original author and original published source. If readers and copyright owners have any objections, please contact us and we will deal with it in a timely manner.

2. The Chinese datasheets provided on the website is a Chinese translation of the English datasheets. Its purpose is for reader's learning exchange only and do not involve commercial purposes. The translation cannot be automatically updated with the original manuscript, and there may also be improper translations. Readers are advised to use the English manuscript as a reference for more accurate information.

3. All product information provided on the website refer to solutions from manufacturers' technical support or users the contents may have differences in description, and readers are advised to take the original article as the standard.

4. If you have any questions, please contact us at marketing@iczoom.com and mark the subject with "Datasheets".



495220 **NPN Epitaxial Silicon Darlington Transistor**

High Voltage & Medium Power Linear Application



Absolute Maximum Ratings * $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
BV _{CBO}	Collector-Base Voltage	550	V
BV _{CEO}	Collector-Emitter Voltage	325	V
BV _{EBO}	Emitter-Base Voltage	10 V	
I _C	Collector Current (DC)	4	А
I _{CP}	Collector Current (Pulse)**	6	А
Ι _Β	Base Current (DC)	0.5	А
P _C	Collector Dissipation(T _C =25°C)	40	w
TJ	Junction Temperature	150	°C
T _{STG}	Storage Junction Temperature Range	- 55 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired. ** Pulse Test : Pulse Width \leq 5ms, Duty Cycle \leq 10%

Electrical Characteristics * T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =1.5A, I _B = 0.05A, L = 25mH	250			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 550V, I_E = 0$			5	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} =10V, I _C =0			1	mA
h _{FE}	DC Current Gain	V _{CE} =5V, I _C =05A V _{CE} =5V, I _C =3.0A	5000 1000			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 0.75A, I_{B} = 0.17A$ $I_{C} = 2A, I_{B} = 5mA$			1.7 1.5	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 2A, I _B = 5mA			2	V

* Pulse Test : Pulse Width ≤ 5ms, Duty Cycle ≤ 10%

April 2008

С



SEMICONDUCTOR

TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx® Build it Now[™] CorePLUS™ CROSSVOLT™ CTL™ Current Transfer Logic™ **EcoSPARK**[®] F Fairchild® Fairchild Semiconductor® FACT Quiet Series™ FACT® FAST® FastvCore™ FPS™ FRFFT® Global Power ResourceSM Green FPS™ Green FPS™ e-Series™ GTO™ i-Lo™ IntelliMAX™ **ISOPLANAR™** MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MillerDrive™ Motion-SPM[™] **OPTOLOGIC[®] OPTOPLANAR[®]** R PDP-SPM™ Power220[®]

Power247[®] POWEREDGE[®] Power-SPM™ PowerTrench® Programmable Active Droop™ **OFFT**® QS™ QT Optoelectronics™ Quiet Series™ RapidConfigure™ SMART START™ SPM[®] STEALTH™ SuperFET™ SuperSOT™-3 SuperSOT[™]-6

SuperSOT[™]-8 SvncFET™ The Power Franchise[®] power

TinyBoost™

TinyBuck™

TinyLogic®

TINYOPTO™

TinyPower™

TinyPWM™

TinyWire™

µSerDes™ UHC®

UniFET™

VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN: NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS, THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be pub- lished at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontin- ued by Fairchild semiconductor. The datasheet is printed for reference infor- mation only.		